

# 4-Ampere N-P-N Darlington Power Transistors

250 and 300 Volts, 50 Watts  
Gain of 500 at 2 A

### Features

- Direct IC input without predriver
- No R<sub>z</sub>, no anti-parallel diode
- Hard glass passivation
- Wire bonded construction

### Applications

- General purpose
- Small engine ignition
- Voltage regulator

The RCA9203A, and RCA9203B\* are monolithic n-p-n silicon Darlington transistors designed for low-and medium-frequency power applications. The construction of these devices provides good forward-bias second-breakdown capability; their high gain makes it possible for them to be driven directly from integrated circuits.

These devices are supplied in the JEDEC TO-220AB (VERSAWATT) plastic package.

\*Formerly RCA Dev. No. TA9203A, and TA9203B.

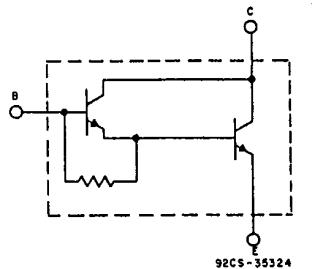
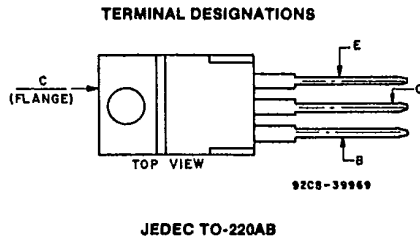


Fig. 1 - Schematic diagram for all types.

### MAXIMUM RATINGS, Absolute-Maximum Values:

	RCA9203A	RCA9203B	UNITS
V <sub>ceo</sub> .....	250	300	V
V <sub>ceo(sus)</sub> .....	250	300	V
V <sub>eso</sub> .....	9	9	V
I <sub>c</sub> .....	4	4	A
I <sub>cm</sub> .....	6	6	A
I <sub>B</sub> .....	0.25	0.25	A
P <sub>r</sub> .....			
T <sub>c</sub> up to 25° C .....	50	50	W
T <sub>c</sub> above 25° C .....	Derate linearly at 0.4		W/°C
T <sub>stg</sub> , T <sub>J</sub> .....	-65 to 150		°C
T <sub>L</sub> .....	235		°C
At distance ≥ 1/8 in. (3.17 mm) from case for 10 s max. ....			

# RCA9203A, RCA9203B

ELECTRICAL CHARACTERISTICS, At Case Temperature ( $T_c$ ) = 25°C

CHARACTERISTIC	TEST CONDITIONS				LIMITS				UNITS
	VOLTAGE V dc		CURRENT A dc		RCA9203A		RCA9203B		
	$V_{CE}$	$V_{BE}$	$I_C$	$I_B$	Min.	Max.	Min.	Max.	
$I_{CBO}$ $I_E = 0$	250 <sup>a</sup> 300 <sup>a</sup>	—	—	—	—	0.2	—	—	mA
$I_{CEO}$	200 250	—	—	0 0	—	0.5	—	0.5	
$I_{EBO}$	—	-9	0	—	—	1	—	1	mA
$V_{CEO(sus)}^c$	—	—	.03 <sup>b</sup>	0	250	—	300	—	V
$h_{FE}$	3.0 3.0	—	2 <sup>b</sup> 4 <sup>b</sup>	—	500 100	—	500 100	—	
$V_{BE}$	3.0	—	4 <sup>b</sup>	—	—	2.5	—	2.5	V
$V_{CE(sat)}$	— —	— —	2 <sup>b</sup> 4 <sup>b</sup>	.1 .2	— —	1.5 2.0	— —	1.5 2.0	V
$C_{obo}$ $V_{CB} = 10$ V $f = 1$ MHz	—	—	—	—	100 Typ.		100 Typ.		pF
$I_{s/b}$ $t = 0.5$ s non- rep. pulse	40	—	—	—	1.25	—	1.25	—	A
$R_{\theta JC}$	—	—	—	—	—	2.5	—	2.5	°C/W

<sup>a</sup> $V_{CB}$  value.

<sup>b</sup>Pulsed, pulse duration = 300  $\mu$ s, duty factor  $\leq$  2%.

<sup>c</sup>Caution: Sustaining voltage,  $V_{CEO(sus)}$ , must not be measured on a curve tracer.

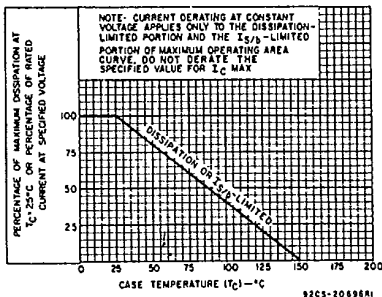


Fig. 2 - Derating curve for all types.

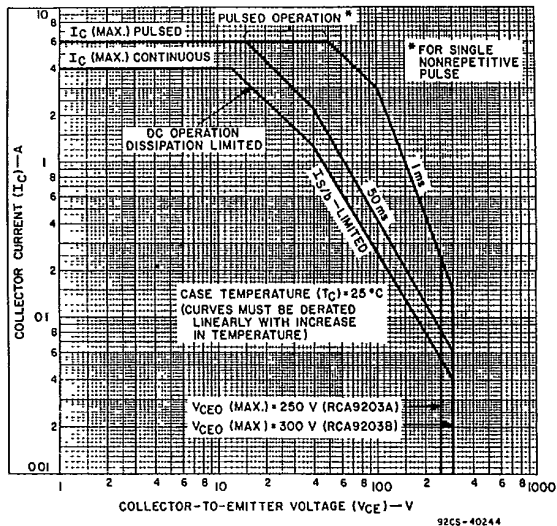


Fig. 3 - Maximum operating areas for all types.

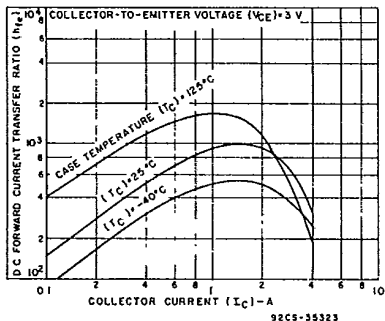


Fig. 4 - Typical dc beta characteristics for all types.

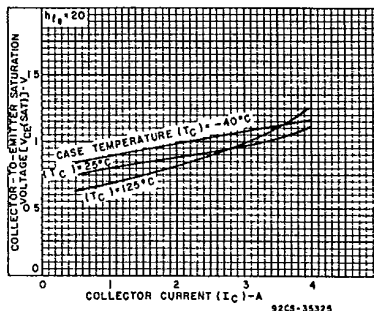


Fig. 5 - Typical saturation characteristics for all types.

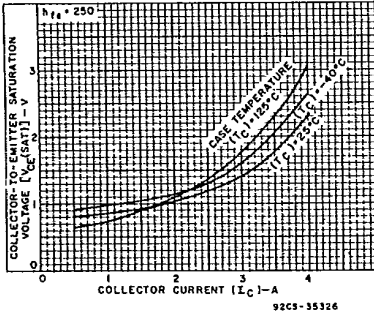


Fig. 6 - Typical saturation characteristics for all types.

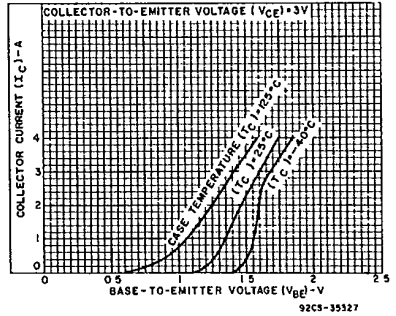


Fig. 7 - Typical transfer characteristics for all types.

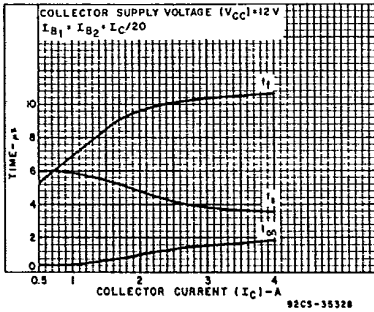


Fig. 8 - Typical saturated switching characteristics for all types.

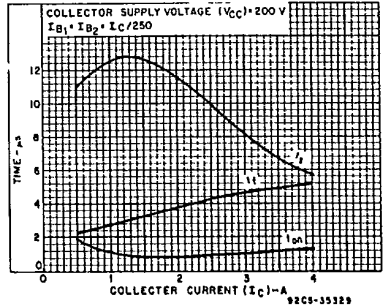


Fig. 9 - Typical saturated switching characteristics for all types.

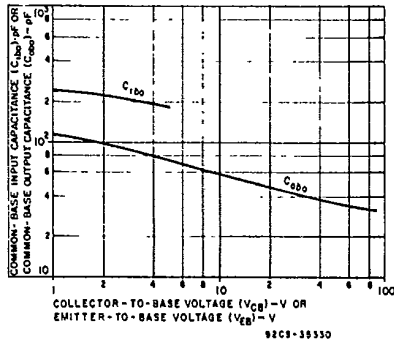


Fig. 10 - Typical common-base input ( $C_{ibo}$ ) or output ( $C_{obo}$ ) capacitance characteristics (all types).